

L Number	Hits	Search Text	DB	Time stamp
1	0	semiconductor with ((carbon adj doped adj oxide) with silcon)	USPAT; US-PGPUB	2004/10/12 07:07
2	0	((carbon adj doped adj oxide) with silcon)	USPAT; US-PGPUB	2004/10/12 07:07
3	298	(carbon adj doped adj oxide)	USPAT; US-PGPUB	2004/10/12 07:07
4	1		USPAT	2004/10/12 08:15
5	1		USPAT	2004/10/12 08:17
6	1		USPAT	2004/10/12 08:18
7	1		USPAT	2004/10/12 08:18
8	1		USPAT	2004/10/12 08:18
9	1		USPAT	2004/10/12 08:19
10	1		USPAT	2004/10/12 08:20
11	1		USPAT	2004/10/12 08:32
12	1		USPAT	2004/10/12 08:32
13	1		USPAT	2004/10/12 09:13
14	1		USPAT	2004/10/12 09:18
15	1		USPAT	2004/10/12 09:18
16	1		USPAT	2004/10/12 09:23
17	1		USPAT	2004/10/12 09:23

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(0) semiconductor with ((carbon adj doped adj oxide) with silc

(0) ((carbon adj doped adj oxide) with silc

(298) (carbon adj doped adj oxide)

(1) "6242351" PN

USPAT:US-PG-PUB

Default operator: OR

(carbon adj doped adj oxide)

USPAT:US-PG-PUB

Default operator: OR

(carbon adj doped adj oxide)

	U	T	Document ID	Issue Date	Pages	Title	Current OR	Current NR	Retrieval C	Inventor	S	C	P	3	4	5
213	<input type="checkbox"/>	<input type="checkbox"/>	US 6740539 B	20040525	6	Carbon-graded layer for impr	438/99	257/E21.277;		Conti, Richard A. et al.	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
214	<input type="checkbox"/>	<input type="checkbox"/>	US 6737728 B	20040518	21	On-chip decoupling capacitor	257/532	257/296;		Block, Bruce A. et al.	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
215	<input type="checkbox"/>	<input type="checkbox"/>	US 6737727 B	20040518	22	Electronic structures with red	257/531	257/532;		Gates, Stephen McCon	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
216	<input type="checkbox"/>	<input type="checkbox"/>	US 6737725 B	20040518	14	Multilevel interconnect struch	257/522	257/618;		Grill, Alfred et al.	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
217	<input type="checkbox"/>	<input type="checkbox"/>	US 6737365 B	20040518	10	Forming a porous dielectric la	438/778	257/E21.273;		Kloster, Grant M. et al.	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
218	<input type="checkbox"/>	<input type="checkbox"/>	US 6734533 B	20040511	9	Electron-beam treated CDO fi	257/632	438/778		Wong, Lawrence D.	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
219	<input type="checkbox"/>	<input type="checkbox"/>	US 6734118 B	20040511	12	Dielectric material treatment	438/795	257/E21.242;		Kloster, Grant M. et al.	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
220	<input type="checkbox"/>	<input type="checkbox"/>	US 6734096 B	20040511	10	Fine-pitch device lithography	438/624	438/634;		Dalton, Timothy J. et al	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
221	<input type="checkbox"/>	<input type="checkbox"/>	US 6726996 B	20040427	7	Laminated diffusion barrier	428/446	428/209;		Barth, Edward Paul et a	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
222	<input type="checkbox"/>	<input type="checkbox"/>	US 6719920 B	20040413	7	Slurry for polishing a barrier l	252/79.1	252/79.4;		Miller, Anne E.	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
223	<input type="checkbox"/>	<input type="checkbox"/>	US 6717265 B	20040406	9	Treatment of low-k dielectric	257/750	257/767		Ingerly, Douglas B. et a	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
224	<input type="checkbox"/>	<input type="checkbox"/>	US 6716771 B	20040406	7	Method for post-CMP conver	438/783	257/E21.241;		Buehler, Mark F. et al.	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
225	<input type="checkbox"/>	<input type="checkbox"/>	US 6713873 B	20040330	15	Adhesion between dielectric	257/758	257/753;		O'Loughlin, Jennifer et	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
226	<input type="checkbox"/>	<input type="checkbox"/>	US 6709721 B	20040323	17	Purge heater design and proce	427/569	257/E21.277;		Rocha-Alvarez, Juan C	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
227	<input type="checkbox"/>	<input type="checkbox"/>	US 6703324 B	20040309	12	Mechanically reinforced high	438/787	257/E21.273;		Wong, Lawrence D.	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
228	<input type="checkbox"/>	<input type="checkbox"/>	US 6703317 B	20040309	6	Method to neutralize charge i	438/716	438/710;		Cheng, Yi-Lung et al.	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
229	<input type="checkbox"/>	<input type="checkbox"/>	US 6703250 B	20040309	7	Method of controlling plasma	438/9	216/58;		Chiu, Hsien-Kuang	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
230	<input type="checkbox"/>	<input type="checkbox"/>	US 6703069 B	20040309	5	Under bump metallurgy for le	427/123	257/737;		Moon, Peter K. et al.	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
231	<input type="checkbox"/>	<input type="checkbox"/>	US 6699797 B	20040302	12	Method of fabrication of low	438/778	257/E21.273;		Morris, Michael A. et al	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
232	<input type="checkbox"/>	<input type="checkbox"/>	US 6693047 B	20040217	7	Method for recycling semicon	438/770	257/E21.251;		Lu, Chih-Cheng et al.	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
233	<input type="checkbox"/>	<input type="checkbox"/>	US 6682989 B	20040127	7	Plating a conductive material	438/454	257/E21.259;		Goodner, Michael D. et	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
234	<input type="checkbox"/>	<input type="checkbox"/>	US 6680262 B	20040120	11	Method of making a semicon	438/780	257/E21.241;		Andideh, Ebrahim et al.	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
235	<input type="checkbox"/>	<input type="checkbox"/>	US 6680164 B	20040120	7	Solvent free photoresist strip	430/329	134/1.1		Nguyen, Huong Thanh	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>

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	U	I	Document ID	Issue Date	Pages	Title	Current OR	Current XR	Retrieval C	Inventor	S	C	P	3
266			US 6528116 B	20030304	38	Lid cooling mechanism and m	427/255.37	257/E21.277,		Pokharna, Himansu et a				
267			US 6522000 B	20030218	4	Method for making a semicon	257/751	257/345,		Jain, Ajay				
268			US 6518171 B	20030211	8	Dual damascene process usin	438/624	438/626,		Towle, Steven N.				
269			US 6500755 B	20021231	14	Resist trim process to define s	438/637	438/444,		Dakshina-Murthy, Srik				
270			US 6486061 B	20021126	39	Post-deposition treatment to e	438/680	257/E21.241,		Xia, Li-Qun et al.				
271			US 6482754 B	20021119	5	Method of forming a carbon d	438/780	257/E21.277,		Andideh, Ebrahim et al.				
272			US 6479391 B	20021112	21	Method for making a dual da	438/706	257/E21.257,		Morrow, Patrick et al.				
273			US 6475930 B	20021105	6	UV cure process and tool for l	438/787	257/E21.241,		Junker, Kurt H. et al.				
274			US 6465372 B	20021015	39	Surface treatment of C-doped	438/787	257/E21.241,		Xia, Li-Qun et al.				
275			US 6455426 B	20020924	4	Method for making a semicon	438/687	257/E21.576,		Jain, Ajay				
276			US 6448185 B	20020910	10	Method for making a semicon	438/706	438/687,		Andideh, Ebrahim et al.				
277			US 6448177 B	20020910	17	Method of making a semicon	438/638	257/E21.579,		Morrow, Patrick et al.				
278			US 6441491 B	20020827	16	Ultralow dielectric constant m	257/759	257/E21.261,		Grill, Alfred et al.				
279			US 6436822 B	20020820	4	Method for making a carbon	438/681	257/E21.261,		Towle, Steven N.				
280			US 6432811 B	20020813	12	Method of forming structural	438/619	257/E21.273,		Wong, Lawrence D.				
281			US 6429117 B	20020806	7	Method to create copper traps	438/627	257/E21.241,		Sudijono, John et al.				
282			US 6417755 B	20020709	18	Method for fabrication of hig	336/200	29/602.1,		Liu, Q. Z. et al.				
283			US 6417098 B	20020709	8	Enhanced surface modificatio	438/638	257/E21.251,		Wong, Lawrence D. et				
284			US 6413852 B	20020702	16	Method of forming multilevel	438/619	257/E21.576,		Grill, Alfred et al.				
285			US 6406993 B	20020618	10	Method of defining small ope	438/624	438/618,		Dakshina-Murthy, Srik				
286			US 6396122 B	20020528	18	Method for fabricating on-chi	257/531	257/528,		Howard, David et al.				
287			US 6391783 B	20020521	6	Method to thin down copper	438/700	257/E21.174,		Sudijono, John et al.				
288			US 6383951 B	20020507	18	Low dielectric constant materi	438/781	257/E21.279,		Li, Weimin				

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